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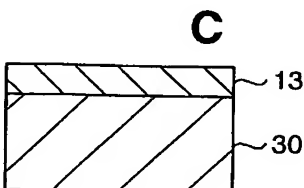
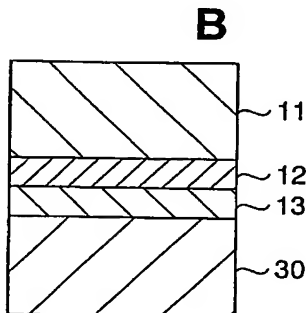
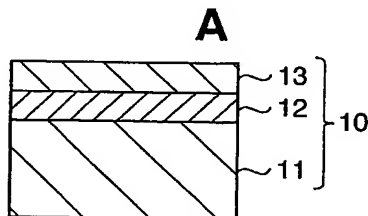
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[Continued on next page]

(54) Title: SEMICONDUCTOR SUBSTRATE, MANUFACTURING METHOD THEREOF, AND SEMICONDUCTOR DEVICE



(57) Abstract: A separation layer is formed on a silicon substrate. An SiGe layer serving as a strain induction layer and a silicon layer serving as a strained semiconductor layer are formed sequentially on the separation layer to prepare a first substrate. The first substrate is bonded to a second substrate made of the same material as the silicon layer of the strained semiconductor layer. The structure is separated into two parts at the separation layer. When the residue of the separation layer and the SiGe layer are removed, and the surface is planarized by hydrogen annealing, an Si substrate having a strained silicon layer on the uppermost surface is obtained.



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